



Package Style: SOT89

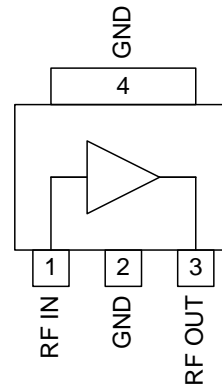


**Features**

- 200MHz to 2200MHz
- +41dBm Output IP3
- 18dB Gain at 900MHz
- +25dBm P1dB
- 2.5dB Typical Noise Figure at 900MHz
- Single 5V Power Supply
- Class 1A ESD Rating (All Pins)

**Applications**

- Broadband MoCA PA
- Linear Driver with Low NF
- High Linearity IF Amplifier



Functional Block Diagram

**Product Description**

The RF3315 is a high-efficiency GaAs Heterojunction Bipolar Transistor (HBT) amplifier packaged in a low-cost surface-mount package. This amplifier is ideal for use in applications requiring high-linearity and low noise figure over the 200MHz to 2200MHz frequency range. This part offers exceptional broadband performance for MoCA applications in the 400MHz to 700MHz and 800MHz to 1500MHz bands. The RF3315 operates from a single 5V power supply.

**Ordering Information**

|               |                                     |
|---------------|-------------------------------------|
| RF3315SQ      | Sample bag with 25 pieces           |
| RF3315SR      | 7" Sample reel with 100 pieces      |
| RF3315TR13    | 13" Reel with 2500 pieces           |
| RF3315PCK-413 | 900MHz PCBA with 5-piece sample bag |

**Optimum Technology Matching® Applied**

- |  |                                      |                                     |                                    |
|--|--------------------------------------|-------------------------------------|------------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT  |
| <input type="checkbox"/> GaAs MESFET         | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    | <input type="checkbox"/> BiFET HBT |
| <input type="checkbox"/> InGaP HBT           | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |                                    |

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## Absolute Maximum Ratings

| Parameter                             | Rating       | Unit |
|---------------------------------------|--------------|------|
| RF Input Power                        | +20          | dBm  |
| Device Voltage                        | -0.5 to +6.0 | V    |
| Device Current                        | 225          | mA   |
| Operating Temperature                 | -40 to +85   | °C   |
| Storage Temperature                   | -40 to +150  | °C   |
| Max. T <sub>J</sub> (MTTF ≥100 years) | 165          | °C   |



**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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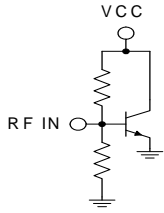
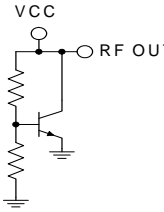


RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

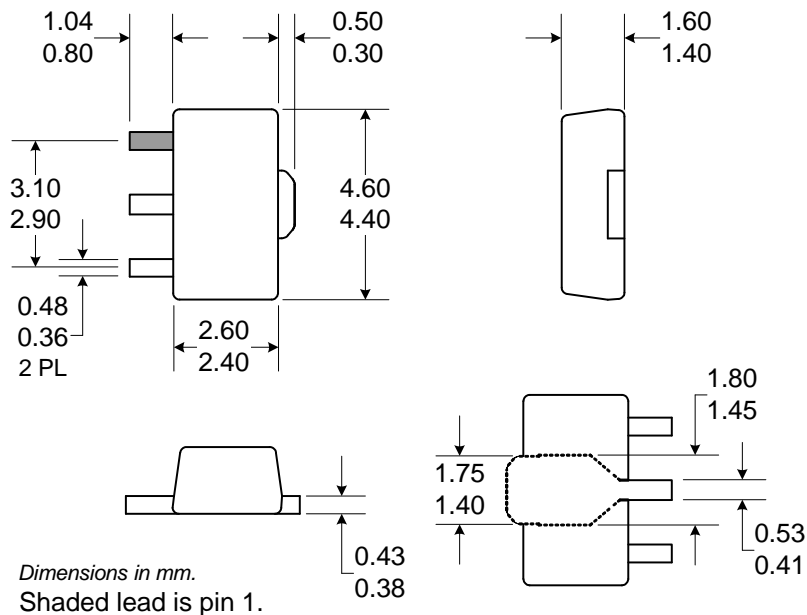
| Parameter   | Specification |       |      | Unit  | Condition  |
|---|---------------|-------|------|-------|--|
|   | Min.          | Typ.  | Max. |       |  |
| <b>Overall</b>  |               |       |      |       |  |
| <b>AC Specifications (2GHz)</b>                             |               |       |      |       | V <sub>CC</sub> = 5V, RF <sub>IN</sub> = -10dBm, Freq = 2.0GHz, with 2GHz application schematic.   |
| Frequency   | 200           |       | 2200 | MHz   |  |
| Gain (Small Signal)   |               | 12.5  |      | dB    | F = 2GHz   |
| Input Return Loss   |               | 15    |      | dB    | F = 2GHz   |
| Output Return Loss  |               | 15    |      | dB    | F = 2GHz   |
| Output IP3  |               | +40.0 |      | dBm   | F <sub>1</sub> = 1.99GHz, F <sub>2</sub> = 2.00GHz, P <sub>IN</sub> = -5dBm                        |
| Output P1dB   |               | +23.0 |      | dBm   |  |
| Noise Figure  |               | 3.0   |      | dB    |  |
|   |               |       |      |       |  |
| <b>AC Specifications (900MHz)</b>                           |               |       |      |       | V <sub>CC</sub> = 5V, RF <sub>IN</sub> = -10dBm, Freq = 900MHz, with 900MHz application schematic. |
| Frequency   |               |       |      | MHz   |  |
| Gain (Small Signal)   | 17            | 18    |      | dB    |  |
| Input Return Loss   |               | 20    |      | dB    |  |
| Output Return Loss  |               | 15    |      | dB    |  |
| Output IP3  | +38.5         | +41   |      | dBm   | F <sub>1</sub> = 900MHz, F <sub>2</sub> = 901MHz, P <sub>IN</sub> = -10dBm                         |
| Output P1dB   | +23.5         | +25.0 |      | dBm   |  |
| Noise Figure  |               | 2.5   |      | dB    |  |
|   |               |       |      |       |  |
| <b>Thermal</b>  |               |       |      |       | I <sub>CC</sub> = 150mA, P <sub>DISS</sub> = 750mW. (See Note.)                                    |
| Theta <sub>JC</sub>   |               | 76    |      | °C/W  |  |
| Maximum Measured Junction Temperature at DC Bias Conditions |               | 142   |      | °C    | T <sub>CASE</sub> = +85°C  |
| Mean Time To Failure  |               | >100  |      | years | T <sub>CASE</sub> = +85°C  |
|   |               |       |      |       |  |
| <b>DC Specifications</b>                                    |               |       |      |       |  |
| Device Voltage  |               | 5.0   |      | V     | I <sub>CC</sub> = 150mA  |
| Operating Current Range                                     | 115           | 150   | 170  | mA    | V <sub>CC</sub> = 5V   |

Note: The RF3315 must be operated at or below 170mA to ensure the highest possible reliability and electrical performance.

**Pin Names and Descriptions**

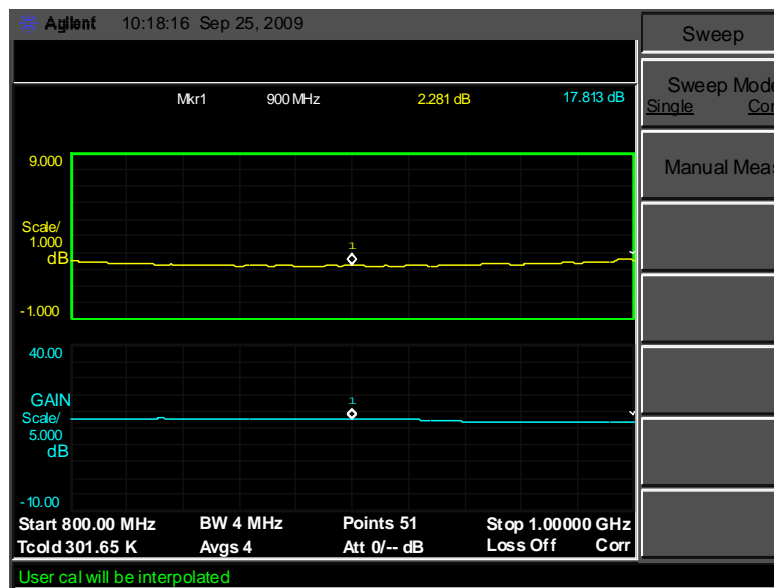
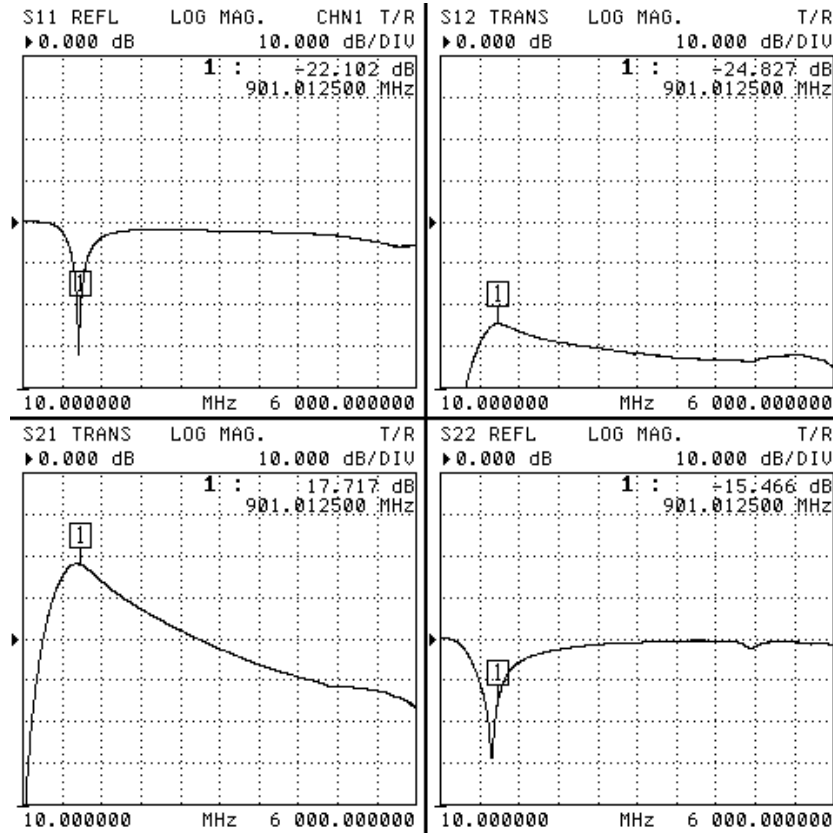
| Pin      | Name   | Description   | Interface Schematic   |
|----------|--------|---|---|
| 1        | RF IN  | RF input pin. This pin is <u>not</u> internally DC-blocked. A DC blocking capacitor, suitable for the frequency of operation, should be used.   |  |
| 2        | GND    | Ground connection.  |   |
| 3        | RF OUT | RF output and bias pin. For biasing, an RF choke is needed. Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used. See application schematic for configuration and value. |  |
| 4        | GND    | Ground connection.  |   |
| Pkg Base | GND    | Ground connection.  |   |

**Package Drawing**



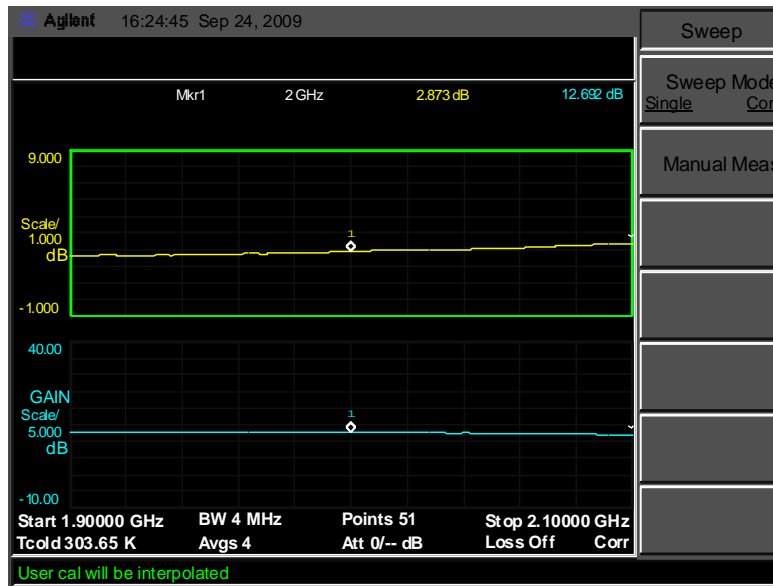
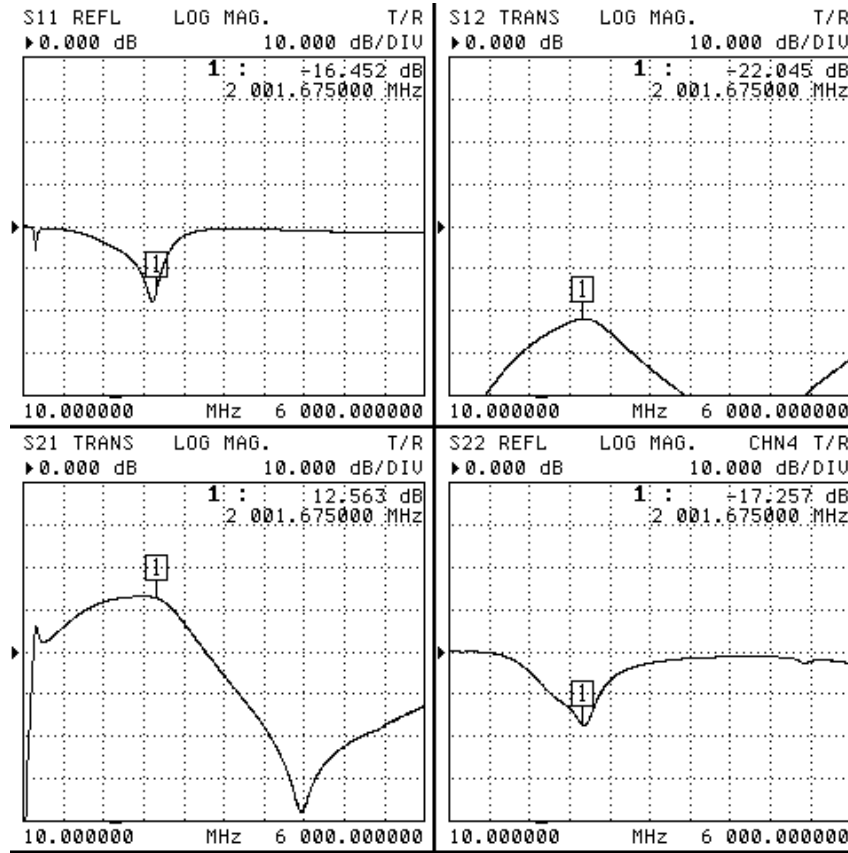
### 900MHz Data

| Frequency (MHz) | V <sub>CC</sub> (V) | I <sub>CC</sub> (mA) | P <sub>IN</sub> (dBm) | P <sub>OUT</sub> (dBm) | Gain (dB) | OIP3 (dBm) | OP1dB (dBm) |
|-----------------|---------------------|----------------------|-----------------------|------------------------|-----------|------------|-------------|
| 900             | 5                   | 149.49               | -9.9                  | 8                      | 17.9      | 41.73      | 24.15       |



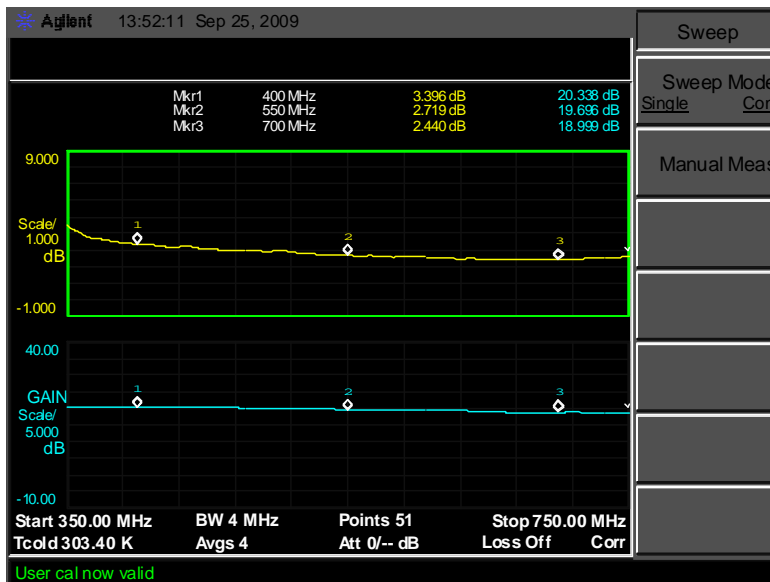
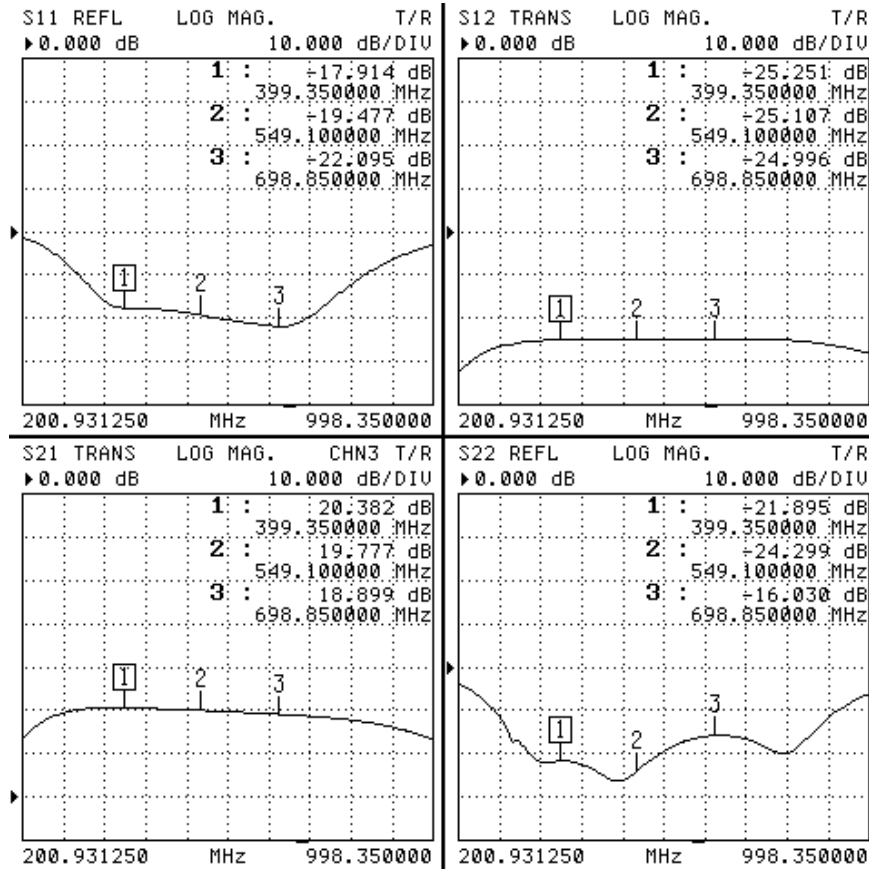
**2GHz Data**

| Frequency (MHz) | V <sub>CC</sub> (V) | I <sub>CC</sub> (mA) | P <sub>IN</sub> (dBm) | P <sub>OUT</sub> (dBm) | Gain (dB) | OIP3 (dBm) | OP1dB (dBm) |
|-----------------|---------------------|----------------------|-----------------------|------------------------|-----------|------------|-------------|
| 2000            | 5                   | 151.53               | -4.88                 | 8                      | 12.89     | 41.4       | 24.76       |



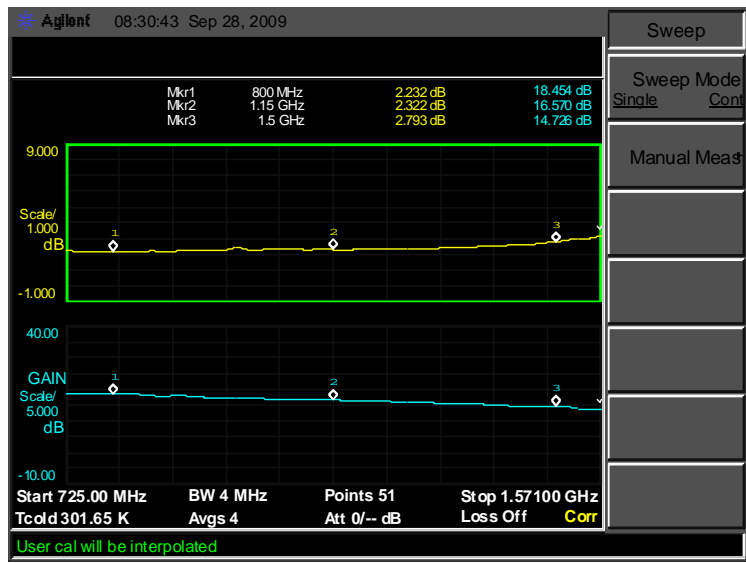
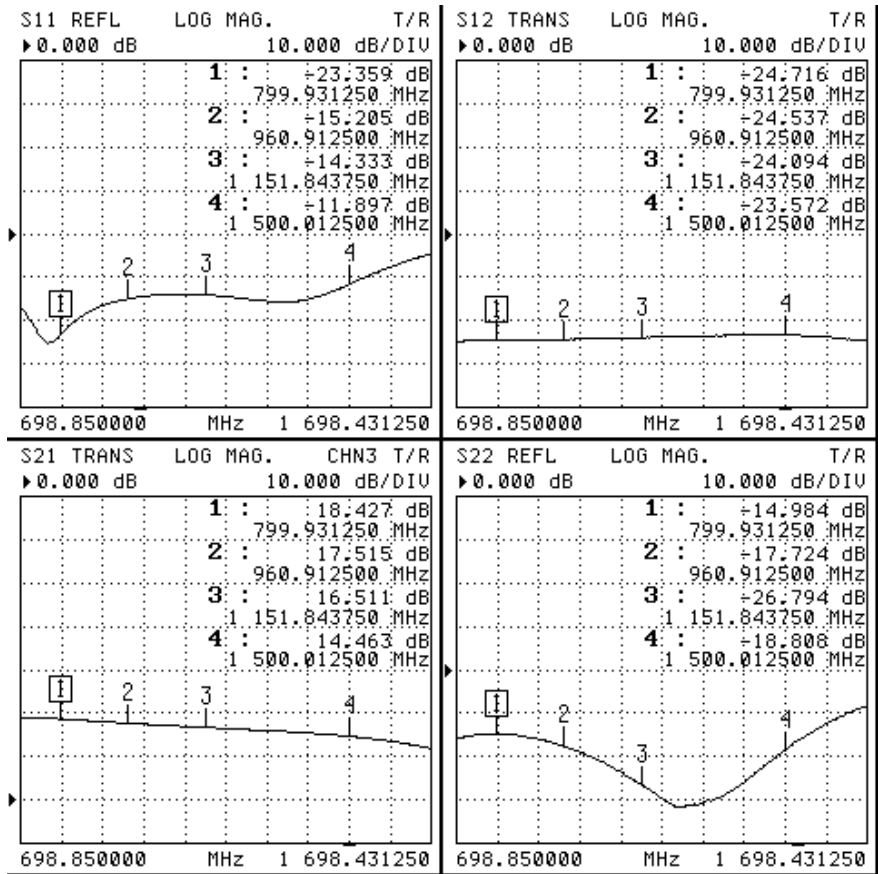
### 400MHz to 700MHz Data

| Frequency (MHz) | V <sub>CC</sub> (V) | I <sub>CC</sub> (mA) | P <sub>IN</sub> (dBm) | P <sub>OUT</sub> (dBm) | Gain (dB) | OIP3 (dBm) | OP1dB (dBm) |
|-----------------|---------------------|----------------------|-----------------------|------------------------|-----------|------------|-------------|
| 400             | 5                   | 147.12               | -12.36                | 8                      | 20.35     | 41.95      | 24.02       |
| 550             | 5                   | 147.47               | -11.64                | 8                      | 19.62     | 40.54      | 24.22       |
| 700             | 5                   | 147.62               | -10.98                | 8                      | 18.96     | 40.59      | 24.94       |

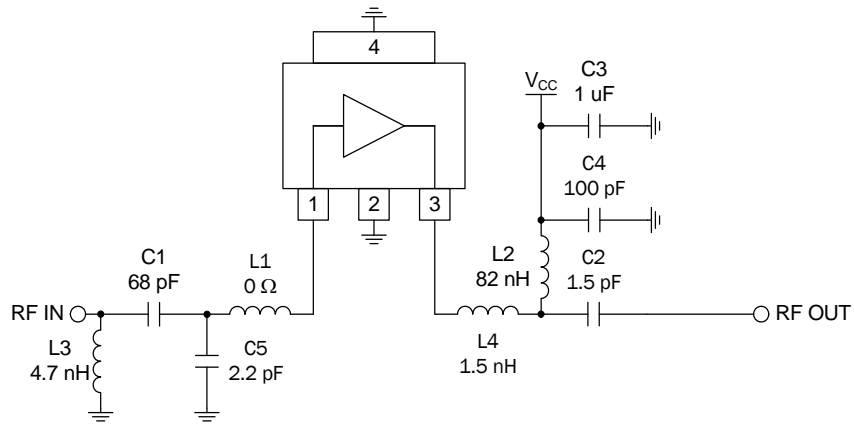


800MHz to 1500MHz Data

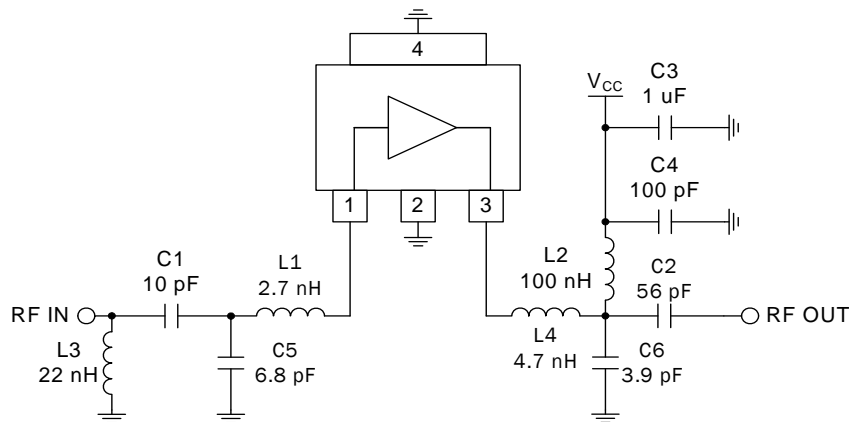
| Frequency (MHz) | V <sub>CC</sub> (V) | I <sub>CC</sub> (mA) | P <sub>IN</sub> (dBm) | P <sub>OUT</sub> (dBm) | Gain (dB) | OIP3 (dBm) | OP1dB (dBm) |   |     |       |   |       |       |       |
|-----------------|---------------------|----------------------|-----------------------|------------------------|-----------|------------|-------------|---|-----|-------|---|-------|-------|-------|
| 800             | 5                   | 148.52               | -10.72                | 8                      | 18.72     | 41.35      | 24.7        |   |     |       |   |       |       |       |
| 960             | 5                   | 148.87               | -9.42                 | 8                      | 17.42     | 42.29      | 25          |   |     |       |   |       |       |       |
| 1150            | 5                   | 149.12               | 8                     | 16.39                  | 42.8      | 25.16      | 1500        | 5 | 149 | -6.22 | 8 | 14.21 | 42.85 | 24.61 |
| 1500            | 5                   | 149                  | -6.22                 | 8                      | 14.21     | 42.85      | 24.61       |   |     |       |   |       |       |       |



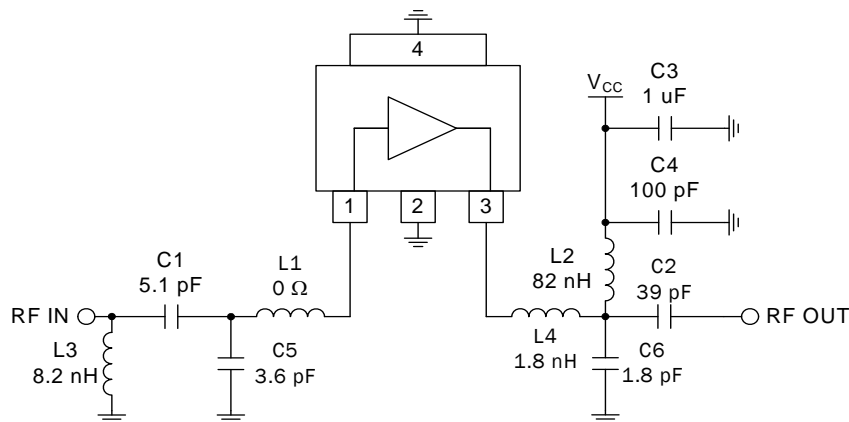
## Typical Application Schematic for 2GHz



## Typical Application Schematic for 400MHz to 700MHz Broadband Match

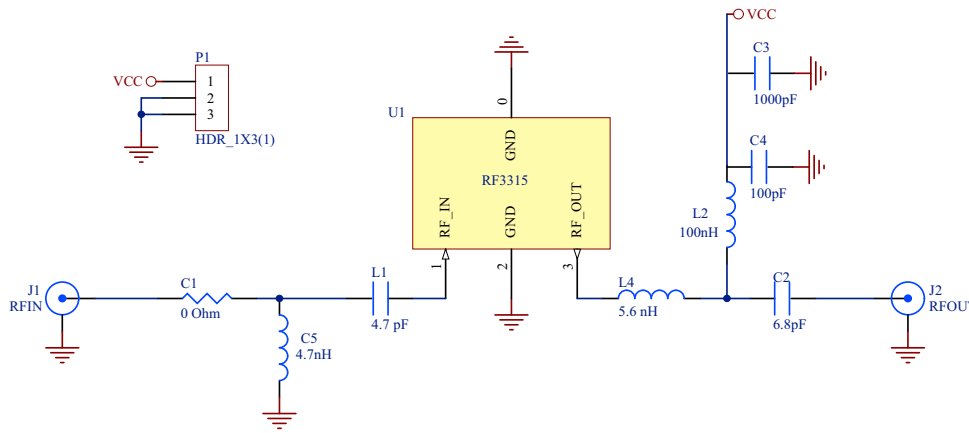


## Typical Application Schematic for 800MHz to 1500MHz Broadband Match





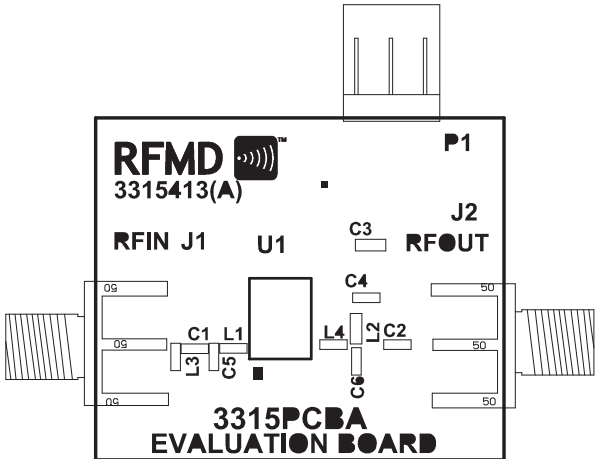
## Evaluation Board Schematic for 900MHz



## Evaluation Board Bill of Materials (BOM) for 900MHz

| Description                           | Reference Designator | Manufacturer                  | Manufacturer P/N    |
|---------------------------------------|----------------------|-------------------------------|---------------------|
| 3315 Evaluation Board                 |                      | Dynamic Details (DDI) Toronto | RF3315413(A)        |
| SOT89, High Linearity Amplifier       | U1                   | RFMD                          | RF3315SB            |
| CAP, 6.8pF, +/-0.1pF, 50V, COG, 0402  | C2                   | Murata Electronics            | GRM1555C1H6R8BZ01E  |
| CAP, 1000pF, 10%, 50V, X7R, 0603      | C3                   | Murata Electronics            | GRM188R71H102KA01D  |
| CAP, 100pF, 5%, 50V, COG, 0402        | C4                   | TDK Corporation               | C1005C0G1H101JT000F |
| CAP, 4.7pF, +/-0.25pF, 50V, COG, 0402 | L1                   | Murata Electronics            | GRM1555C1H4R7CZ01E  |
| RES, 0Ω, 0402                         | C1                   | Panasonic Industrial Devices  | ERJ-2GE0R00         |
| IND, 4.7nH, 5%, W/W, 0402             | C5                   | Coilcraft                     | 0402CS-4N7XJLW      |
| IND, 100nH, 5%, W/W, 0603             | L2                   | Coilcraft                     | 0603CS-R10XJBC      |
| IND, 5.6nH, 5%, W/W, 0402             | L4                   | Coilcraft                     | 0402CS-5N6XJLW      |
| CONN, SMA, END LNCH, RND, 0.031"      | J1-J2                | Emerson Network Power         | 142-0701-881        |
| CONN, HDR, ST, PLRZD, 3-PIN, 0.100"   | P1                   | ITW Pancon                    | MPSS100-3-C         |
| DNP                                   | C6, L3               | N/A                           | N/A                 |

## Evaluation Board Layout for 900MHz Board Size 1.195" x 1.000" Board Thickness 0.033", Board Material FR-4



## PCB Design Requirements

### PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

### PCB Land Pattern Recommendation

PCB land patterns are based on IPC-SM-782 standards when possible. The pad pattern shown has been developed and tested for optimized assembly at RFMD; however, it may require some modifications to address company specific assembly processes. The PCB land pattern has been developed to accommodate lead and package tolerances.

### PCB Metal Land Pattern

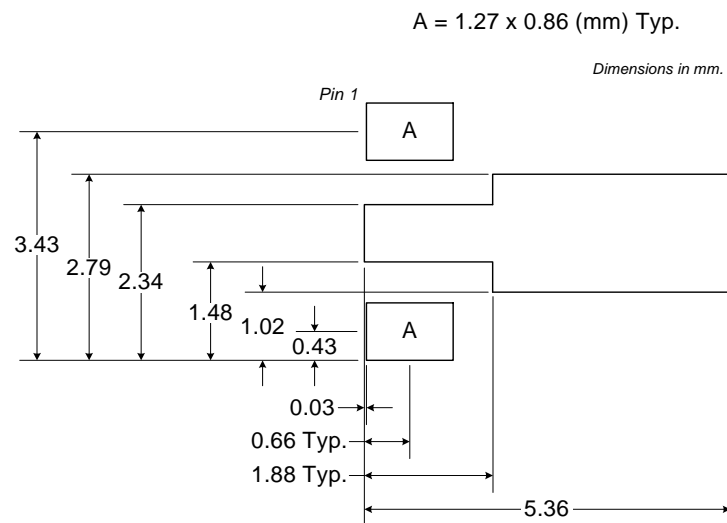


Figure 1. PCB Metal Land Pattern (Top View)

### PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

A = 1.37 x 0.96 (mm) Typ.

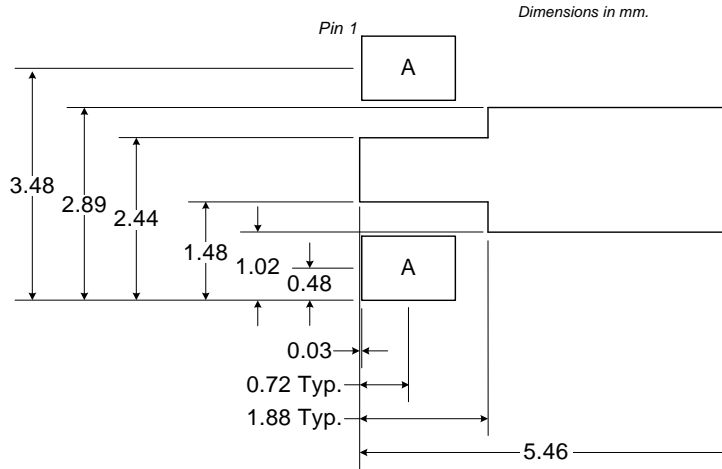


Figure 2. PCB Solder Mask Pattern (Top View)

### Thermal Pad and Via Design

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

